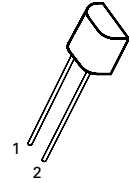
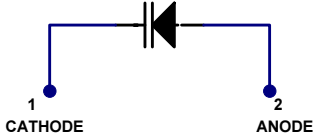


SILICON EPITAXIAL PLANAR ABRUPT TUNER DIODE

ZC744

ISSUE 2 – SEPTEMBER 94

DIODE PIN CONNECTION



**E-Line
TO92 Compatible**

ELECTRICAL CHARACTERISTICS (at $T_{amb}=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Reverse Breakdown Voltage	V_R	30			V	$I_R=10\mu\text{A}$
Reverse Voltage Leakage	I_R			0.02	μA	$V_R=25\text{V}$
Case Capacitance	C_C		0.15		pF	
Temperature Coefficient of capacitance	η		0.02		$\%/\text{C}$	$V_R=3\text{V}$

TUNING CHARACTERISTICS (at $T_{amb}=25^{\circ}\text{C}$)

PART NO.	C_1 at $V_R=4\text{V}$, $f=1\text{MHz}$ pF			Capacitance Ratio C_2/C_{30} at $f=1\text{MHz}$	Minimum Q at $V_R=4\text{V}$ $f=50\text{MHz}$
	MIN	TYP	MAX		
ZC744	13.5	15.0	16.5	2.8	400

TYPICAL CHARACTERISTICS

